

## R-C Thermal Model Parameters

### DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

*Note:*

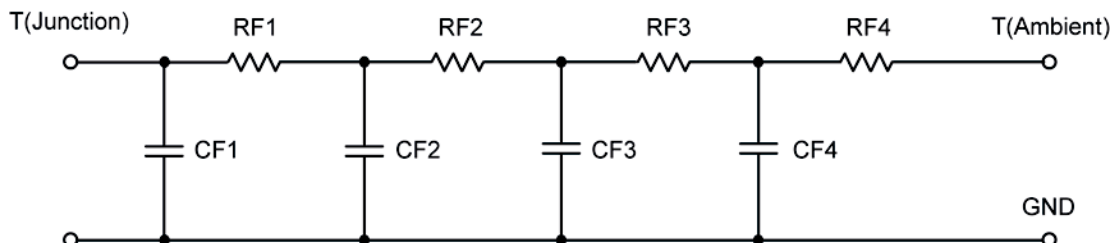
*For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).*

### R-C THERMAL MODEL FOR TANK CONFIGURATION



<b>R-C VALUES FOR TANK CONFIGURATION</b>			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	7.8092	N/A	13.7868
RT2	23.1315	N/A	4.3985
RT3	27.8929	N/A	13.7401
RT4	50.8875	N/A	8.3180
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	665.4582 u	N/A	5.8132 m
CT2	115.4287 m	N/A	430.5131 u
CT3	13.5551 m	N/A	55.2649 m
CT4	1.1187	N/A	215.4369 m

*This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.*

**R-C THERMAL MODEL FOR FILTER CONFIGURATION****R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	8.7032	N/A	5.1975
RF2	30.4976	N/A	16.8150
RF3	22.3850	N/A	9.1510
RF4	47.9775	N/A	8.7791
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	670.3049 u	N/A	430.6036 u
CF2	11.0549 m	N/A	4.8667 m
CF3	74.7262 m	N/A	44.6543 m
CF4	1.0086	N/A	35.9846 m

Note: NA indicates not applicable

## Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya, IEEE / SEMITHERM 2002

